

4N25M, 4N26M, 4N27M, 4N28M, 4N35M, 4N36M, 4N37M, H11A1M, H11A2M, H11A3M, H11A4M, H11A5M General Purpose 6-Pin Phototransistor Optocouplers

Features

- UL recognized (File # E90700, Volume 2)
- VDE recognized (File # 102497)
- Add option V (e.g., 4N25VM)

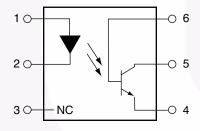
Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs

Description

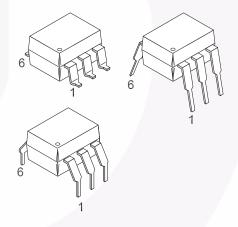
The general purpose optocouplers consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line package.

Schematic



- PIN 1. ANODE
 - 2. CATHODE
 - 3. NO CONNECTION
 - 4. EMITTER
 - 5. COLLECTOR
 - 6. BASE

Package Outlines



Absolute Maximum Ratings (T_A = 25°C unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Units	
TOTAL DEV	ICE		•	
T _{STG}	Storage Temperature	-40 to +150	°C	
T _{OPR}	Operating Temperature	-40 to +100	°C	
T _{SOL}	Wave solder temperature (see page 8 for reflow solder profile)	260 for 10 sec	°C	
P _D	Total Device Power Dissipation @ T _A = 25°C	250	mW	
	Derate above 25°C	2.94	1	
EMITTER			·	
I _F	DC/Average Forward Input Current	60	mA	
V _R	Reverse Input Voltage	6	V	
I _F (pk)	Forward Current – Peak (300µs, 2% Duty Cycle)	3	А	
P _D	LED Power Dissipation @ T _A = 25°C	120	mW	
	Derate above 25°C	1.41	mW/°C	
DETECTOR				
V _{CEO}	Collector-Emitter Voltage	30	V	
V _{CBO}	Collector-Base Voltage	70	V	
V _{ECO}	Emitter-Collector Voltage	7	V	
P _D	Detector Power Dissipation @ T _A = 25°C	150	mW	
	Derate above 25°C	1.76	mW/°C	

Electrical Characteristics (T_A = 25°C unless otherwise specified)

Individual Component Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.*	Max.	Unit
EMITTER						
V _F	Input Forward Voltage	I _F = 10mA		1.18	1.50	V
I _R	Reverse Leakage Current	$V_{R} = 6.0V$		0.001	10	μΑ
DETECTOR					7	
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 1.0mA, I _F = 0	30	100		V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_F = 0$	70	120		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	$I_E = 100 \mu A, I_F = 0$	7	10		V
I _{CEO}	Collector-Emitter Dark Current	$V_{CE} = 10V, I_F = 0$		1	50	nA
I _{CBO}	Collector-Base Dark Current	V _{CB} = 10V			20	nA
C _{CE}	Capacitance	$V_{CE} = 0V, f = 1 MHz$		8		pF

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.*	Max.	Units
V _{ISO}	Input-Output Isolation Voltage	f = 60Hz, t = 1 sec	7500			Vac(pk)
R _{ISO}	Isolation Resistance	V _{I-O} = 500 VDC	10 ¹¹			Ω
C _{ISO}	Isolation Capacitance	$V_{I-O} = \&, f = 1MHz$		0.2	2	pF

^{*}Typical values at T_A = 25°C

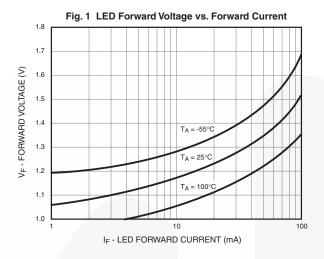
$\textbf{Electrical Characteristics} \text{ (Continued) (} T_{A} = 25^{\circ}\text{C unless otherwise specified)}$

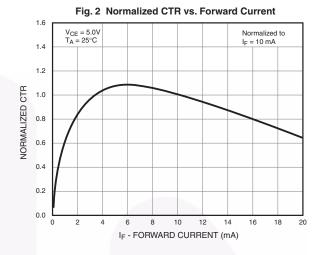
Transfer Characteristics

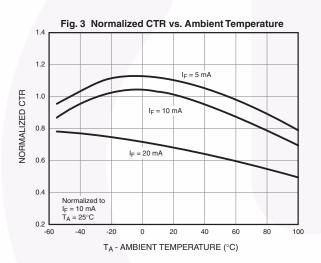
Symbol	Parameter	Test Conditions	Device	Min.	Typ.*	Max.	Unit
DC CHARA	ACTERISTICS						
CTR	Current Transfer Ratio, Collector to Emitter	I _F = 10mA, V _{CE} = 10V	4N35M, 4N36M, 4N37M	100			%
			H11A1M	50			
			H11A5M	30			
			4N25M, 4N26M H11A2M, H11A3M	20			
			4N27M, 4N28M H11A4M	10			
		$I_F = 10$ mA, $V_{CE} = 10$ V, $T_A = -55$ °C	4N35M, 4N36M, 4N37M	40			
		$I_F = 10$ mA, $V_{CE} = 10$ V, $T_A = +100$ °C	4N35M, 4N36M, 4N37M	40			
V _{CE (SAT)}	Collector-Emitter Saturation Voltage	$I_C = 2mA, I_F = 50mA$	4N25M, 4N26M, 4N27M, 4N28M,			0.5	V
		$I_C = 0.5 \text{mA}, I_F = 10 \text{mA}$	4N35M, 4N36M, 4N37M			0.3	
			H11A1M, H11A2M, H11A3M, H11A4M, H11A5M			0.4	
AC CHARA	ACTERISTICS						
T _{ON}	Non-Saturated Turn-on Time	$I_F = 10 \text{mA}, V_{CC} = 10 \text{V},$ $R_L = 100 \Omega \text{ (Fig. 11)}$	4N25M, 4N26M, 4N27M, 4N28M, H11A1M, H11A2M, H11A3M, H11A4, H11A5M		2		μs
		$I_C = 2mA, V_{CC} = 10V,$ $R_L = 100\Omega$ (Fig. 11)	4N35M, 4N36M, 4N37M		2	10	μs
T _{OFF}	Turn-off Time	$I_F = 10 \text{mA}, V_{CC} = 10 \text{V},$ $R_L = 100 \Omega \text{ (Fig. 11)}$	4N25M, 4N26M, 4N27M, 4N28M, H11A1M, H11A2M, H11A3M, H11A4M, H11A5M		2		μs
		$I_C = 2mA, V_{CC} = 10V,$ $R_L = 100\Omega$ (Fig. 11)	4N35M, 4N36M, 4N37M		2	10	

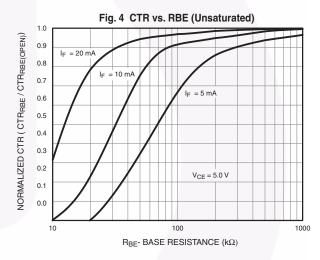
^{*} Typical values at T_A = 25°C

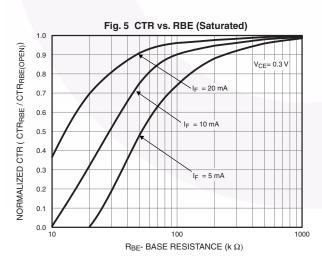
Typical Performance Curves

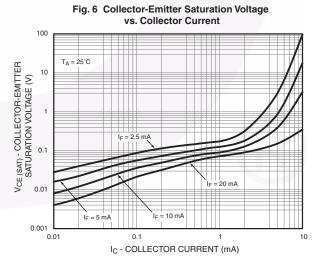


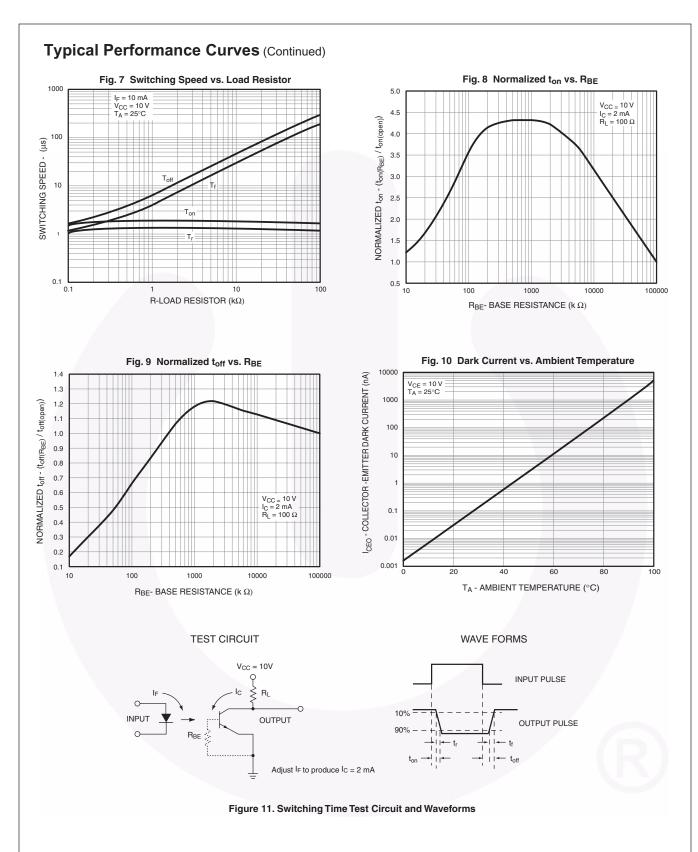






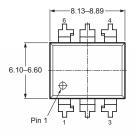


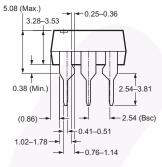


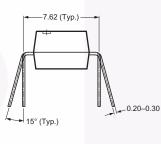


Package Dimensions

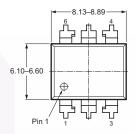
Through Hole

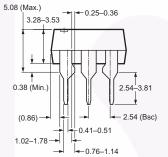


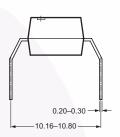




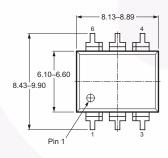
0.4" Lead Spacing

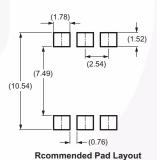


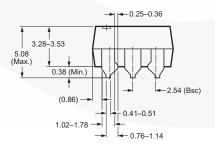


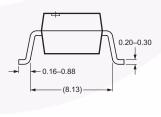


Surface Mount







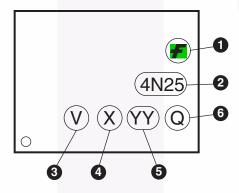


Note: All dimensions in mm.

Ordering Information

Option	Order Entry Identifier (Example)	Description
No option	4N25M	Standard Through Hole Device
S	4N25SM	Surface Mount Lead Bend
SR2	4N25SR2M	Surface Mount; Tape and Reel
Т	4N25TM	0.4" Lead Spacing
V	4N25VM	VDE 0884
TV	4N25TVM	VDE 0884, 0.4" Lead Spacing
SV	4N25SVM	VDE 0884, Surface Mount
SR2V	4N25SR2VM	VDE 0884, Surface Mount, Tape and Reel

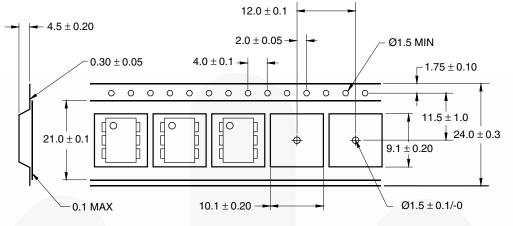
Marking Information



Definitions				
1	Fairchild logo			
2	Device number			
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)			
4	One digit year code, e.g., '7'			
5	Two digit work week ranging from '01' to '53'			
6	Assembly package code			

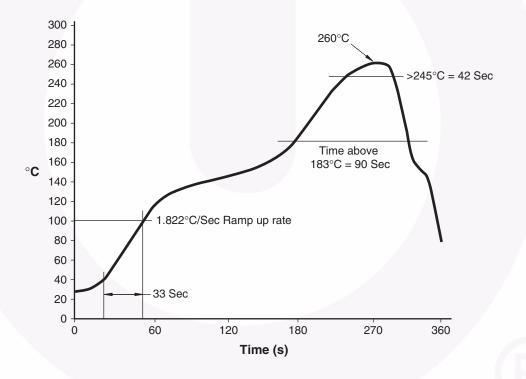
*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.

Carrier Tape Specification



User Direction of Feed _____

Reflow Profile







Dana It 140W

CorePLUS™ CorePOWER™ CROSSVOLT™

Current Transfer Logic™ EcoSPARK[®] EfficentMax™ EZSWITCH™ *

E7™ **/**F®

Fairchild[®]

Fairchild Semiconductor[®] FACT Quiet Series™

FACT[®]
FAST[®]
FastvCore™
FlashWriter^{®*}
FPS™
F-PFS™

Global Power Resource $^{\rm SM}$ Green FPS $^{\rm TM}$

Green FPS™ e-Series™

GTO™ IntelliMAX™ ISOPLANAR™ MegaBuck™

MICROCOUPLER™ MicroFET™

MicroPal™
MicroPak™
MillerDrive™
MotionMax™
Motion-SPM™
OPTOLOGIC®
OPTOPLANAR®

PDP SPM™
Power-SPM™
PowerTrench®
PowerXS™

Togrammable Melive Droop

QFET[®] QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SmartMax™

SMART START™
SPM®
STEALTH™

SuperFETTM
SuperSOTTM-3
SuperSOTTM-6
SuperSOTTM-8
SupreMOSTM
SyncFETTM
SYSTEM ®

The Power Franchise®

Franchise

TinyBoost™
TinyBuck™
TinyLogie®
TINYOPTO™
TinyPower™
TinyPWM™
TinyPWI™
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